

(19)  
(12)(KR)  
(A)(51) 。 Int. Cl. <sup>7</sup>  
H05B 33/22(11)  
(43)2003 - 0029467  
2003 04 14(21) 10 - 2002 - 0060026  
(22) 2002 10 02

(30) JP - P - 2001 - 00307516 2001 10 03 (JP)

(71) 가 가  
5 7 1(72)  
5 - 7 - 1 가 가  
5 - 7 - 1 가 가  
5 - 7 - 1 가 가

(74)

:

(54) ,

가

, ,

( EL ) ,

(zone)

,

,

,

가

.

2

EL ,

1 EL .

2 .

3 .

4 (zone plate) .

5 .

6 5 .

7 .

, , (EL) .

EL 가 (self light device) .

VanS1yke, C.W.Tang EL (C.W.Tang, S.A, (App1ied Physics Letters), 51 , 913 , 1987 )가 (8 - ; 8 - quinolinol) , Tang (exciton) , ( ) 가 .

EL ( ) 3 ( ) , 2 , ( ) , , 가 .

te) , 가 . (single excited sta  
25%  
1  
1.6  
2  
0% , 5%  
( ) 「 , vo 1. 1, No. 3,  
p11, 1995 9 ).

가  
63 - 314795 ) 가 , ( 1 - 220394 )  
, 가  $\mu\text{m}$  가  
가 가  
가 .

, ( 62 - 1  
72691 ) , 가  
가 .

, EL 가 .  
3

1 EL  
2  
L ( ) .  
( EL ) . 3 E

(natural pictuer) (R), (G), (B)  
1 RGB 5 - 275172 , 5 - 25  
8859 , 2 - 258860 RGB 가

, 2, 3  
- 220871 EL 2 가 7  
3 - 152897 11 - 121164 3 .

, 2, 3 EL  
가  
가

가 . EL 가

가 .

EL

EL

가 . ( 11 - 8070 ),

가 .

가 EL

가

가

( EL ) ,  
(zone plate) ,

가

2 , 1 , 가

가

3 , 1 , 1 ,

가 ,

4 , 3 ,

5 , 1 , 2 (cyc

le)

6 , 1 , 가

가

7 , 1 가 , , ,  
 , 가 , , 가  
 , 가 .

8 , 1 , ,  
 가 .

9 , 1 ,  
 가 .

10 , 1, 2, 5, 7, 8, 9  
 가 .

11 , 1, 3, 4, 5, 6, 8, 9  
 가 .

12 , 1, 2, 5, 7, 8  
 , 1, 7, 8, 9 가  
 .

13 , 1, 3, 4, 5, 6  
 , 1, 6, 8, 9 가  
 .

14 , 1, 2, 5, 7, 8  
 , 1, 7, 8, 9 가 가  
 , 가  
 .

15 , 1, 3, 4, 5, 6  
 , 1, 6, 8, 9 가 가  
 , 가  
 .

, 가 . 2991183 EL  
 . EL (zone plate)  
 , EL  
 . EL  
 , 가 .

2 (5) (1)  
 2 (5)  
 (3) (2) (3) (6) (6)  
 (5) (laminary type) (taper)가 (blade)가 2가  
 3 (5) (1) (2), (3 ; ), (4) (6)가 (1)가  
 (5) (5) (1) (2) (2) (2) (2) (5) (2)  
 (gold) (2) (3) (4) (2)가 (5)  
 (5)가 (5) (5) (5)  
 (5) (5) EL가 (5)  
 0.5  
 가 (groove) 4 (zone plate) 4 (5)가  
 (1)  
 (5) (5)가 (3) (6) (6)가 (5) (2), (6)가  
 EL ; 3), (4) (1) (6) (1)

[illegible]

Figure 1 consists of two parts: (a) a schematic diagram of the device structure and (b) an energy band diagram. Part (a) shows a cross-section of the device with layers: p-Si substrate, p-Si layer, n-Si layer, and p-Si layer. The bottom part shows the energy band diagram with conduction band (CB) and valence band (VB) levels. The diagram is labeled with (a) and (b).

EL

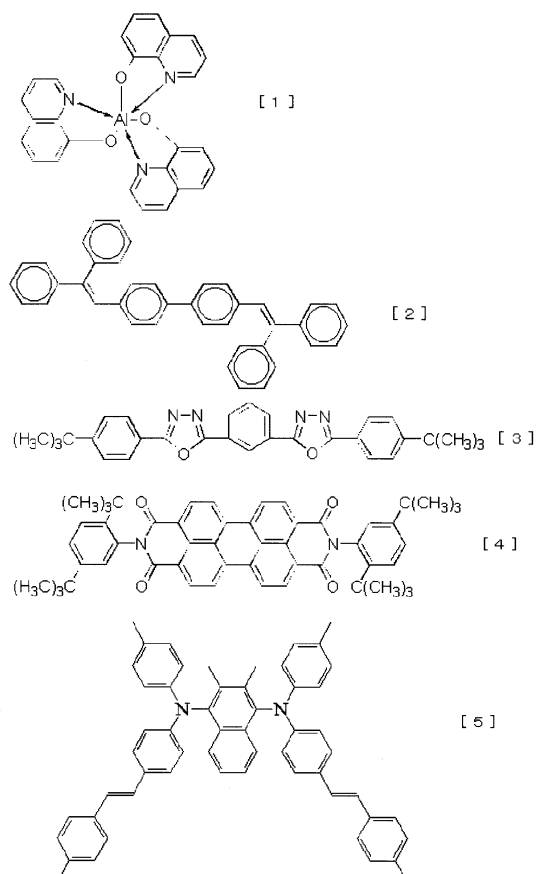
1

2

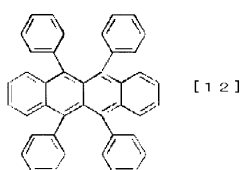
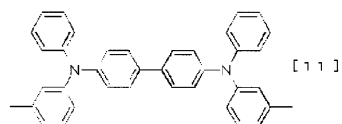
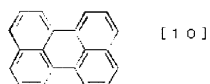
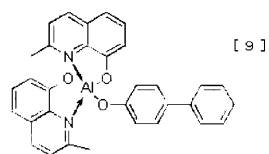
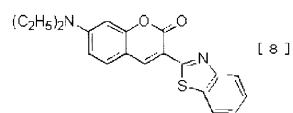
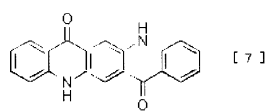
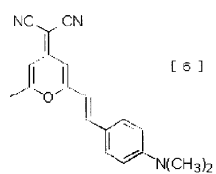
$$(\quad),$$
$$(\quad, \quad, \quad, \quad)$$

(BDPVBi) [2], 1,3 - (p - t - - 1,3,4 - ) (OXD - ) [3], N,N' - (2,5 - - t - ) (BPPC) [4], 1,4 (p - - p - ) [5] (Alq3) [1]

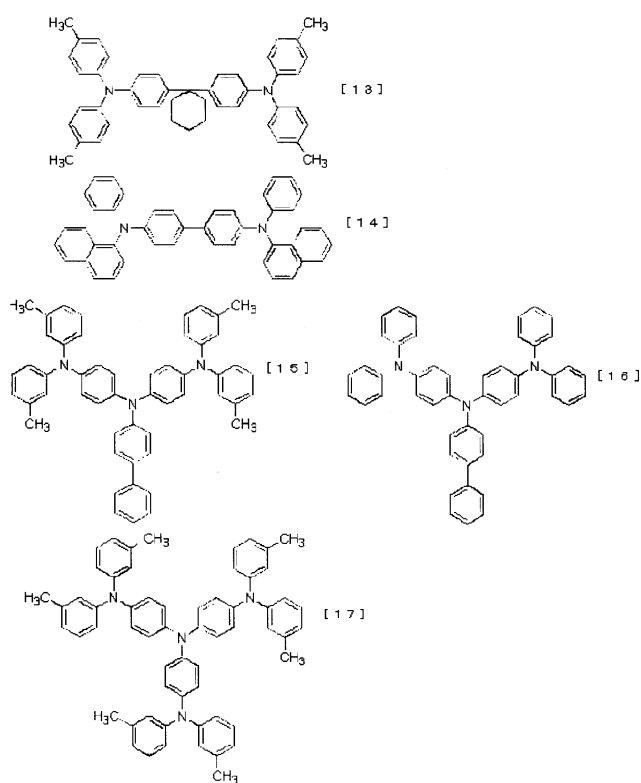




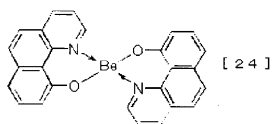
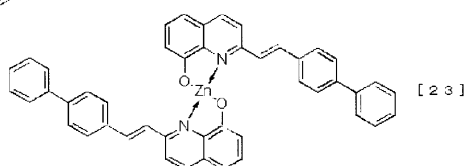
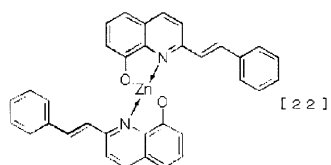
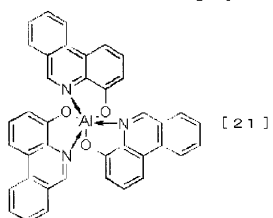
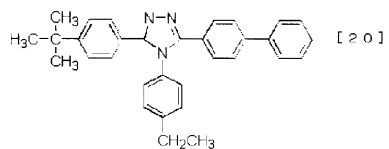
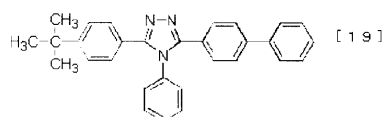
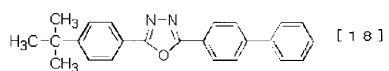
Alq3[1]  
 4 - 2 - 6 - (p - ) - 4H - (DCM)[6], 2,3 - [7]  
 , 3 - (2' - ) - 7 - [8]  
 (2 - 8 - ) - 4 - [9] [10]  
 , 4,4' - (m - ) (TPD)[11] [12]



[17] (1 - ) - 1,1' - , ( (p - ) ) - 1,1 - [13], TPD[11], N.N - - N - N ([15]) - 4,4 - (NPB)[14] ,



3] , 2 - (4 - ) - 5 - (4 - t - ) - 1,3,4 - (Bu - PBD)[18], OXD - 7[  
 ) , ([19], [20] ), ([1], [9], [21] [24]



EL

EL

(MBE )

EL

10nm

1

, ( EL ) 1 가 . 50mm x 25mm (HOYA  
 , NA45, 1.1mm ) G ( ) , AZTFP650F5)

, 280nm 가 (groove) 280nm  
 , 500nm  
 , EL 가  
 100nm ITO , 20 /  
 ITO 200 $\mu$ m , 100 $\mu$ m , 250mm  
 가 38 30  
 $5 \times 10^{-7}$  Torr 가  
 0.15nm  
 가 40nm [14] 70nm  
 [2] , 40nm  
 [1]  
 , (silver) (boat)  
 , (silver) 1.0nm, 0.2nm  
 , 200nm , 200 $\mu$ m,  
 100 $\mu$ m ITO( )  
 가  
 5 (6) 5 (6)  
 5 (6) (6A), (6B),  
 (6C) (6A, 6B, 6C) 200 $\mu$ m (6A) (6B)  
 (6B) (6C) 100 $\mu$ m (6) 200 $\mu$ m 100 $\mu$ m  
 (6A) 3 - (2' - ) - 7 - , (6B)  
 ( 6C) 6 5 (6C) (copper) -  
 (6C) 가 6 (6)가  
 (6) (6A, 6B, 6C) ITO (8)가  
 1 ( EL ) 8V 가 ,  
 (6A, 6B, 6C) , 180, 45, 53cd/m<sup>2</sup>

1 ( EL ) 2 가 . 2 ,  
 280nm 275nm 1 ,  
 8V 가 , (6A, 6B, 6C) (red - oran  
 ge) , 240, 60, 70cd/m<sup>2</sup> .

3  
 , ( EL ) 3 가 . 3 , 1  
 280nm , ,  
 가 (siver) 1 200nm ,  
 - (siver) 1 , ITO( ) 1  
 . ITO 1 (6) (6) ITO  
 O.1mm , (6A, 6B, 6C)가 ITO  
 6C) 3 8V 가 , (6A, 6B,  
 160, 40, 47cd/m<sup>2</sup> .

4  
 , ( EL ) 4 . 4 ,  
 3 280nm 275nm 3 ,  
 4 8V 가 , (6A, 6B, 6C) ,  
 220, 55, 67cd/m<sup>2</sup> .

5  
 ( EL ) 5 가 . 7  
 . 7 , 2 . 5 , 7  
 8V 2 가 , (6A, 6B, 6C) , 5 280,  
 70, 80cd/m<sup>2</sup> .

6  
 ( EL ) 6 가 . 6 , 7  
 4 가 , (6A, 6B, 6C) , 6 300, 75,  
 8V 가 , 90cd/m<sup>2</sup> .

가

(57)

1.

,

( EL ) ,

(zone

plate) ,

,

,

.

2.

1

,

,

가

,

가

,

가

.

3.

1

,

,

가

,

가

,

.

4.

3

,

.

5.

1

,

2

(cycle)

.

6.

1 ,

가 , ,

가 .

7.

1 ,

, , 가 , , 가 , 가 , 가 .

8.

1 ,

, .

9.

1 ,

.

10.

,

1, 2, 5, 7, 8, 9

.

11.

,

1, 3, 4, 5, 6, 8, 9

.

12.

,

1, 2, 5, 7

, 1, 7, 8, 9 가

.

13.



1, 3, 4, 5, 6

, 1, 6, 8, 9

가

14.

1, 2, 5, 7

, 1, 7, 8, 9

가

가

가

15.

1, 3, 4, 5, 6

, 1, 6, 8, 9

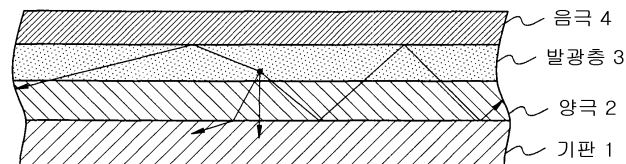
가

가

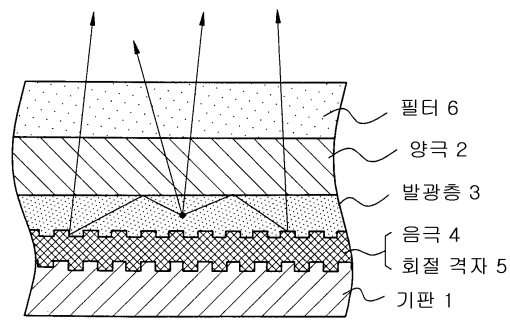
가

1

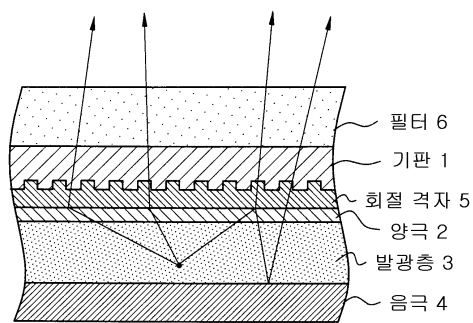
종래기술



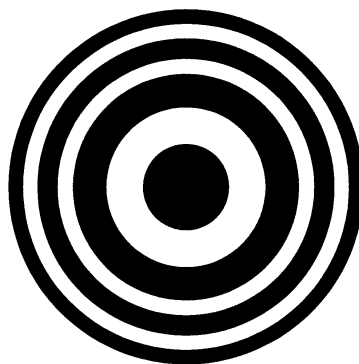
2



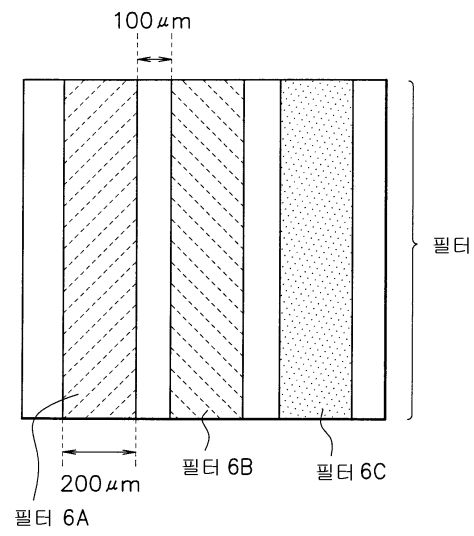
3



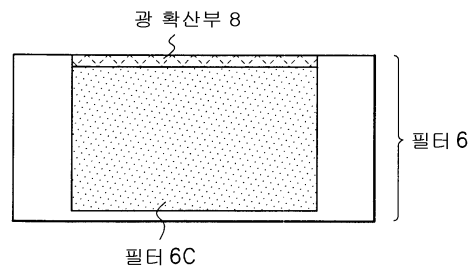
4



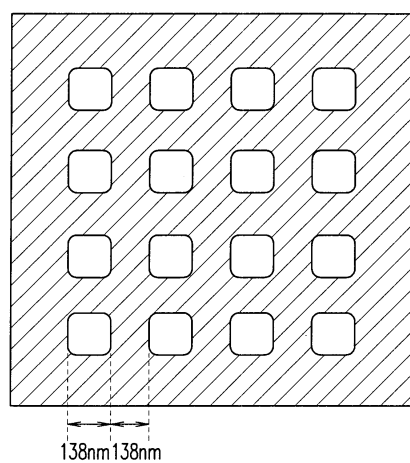
5



6



7



专利名称(译)	发光元件，制造该元件的方法		
公开(公告)号	<a href="#">KR1020030029467A</a>	公开(公告)日	2003-04-14
申请号	KR1020020060026	申请日	2002-10-02
申请(专利权)人(译)	三星SD眼有限公司		
当前申请(专利权)人(译)	三星SD眼有限公司		
[标]发明人	TOGUCHI SATORU 토구치사토루 ISHIKAWA HITOSHI 이시카와히토시 ODA ATSUSHI 오다아쯔시		
发明人	토구치사토루 이시카와히토시 오다아쯔시		
IPC分类号	H05B33/02 H01L51/50 H05B33/22 H01L27/32 H05B33/26 H05B33/24 G09F9/30 G09F9/00 H01L51/52 H05B33/12		
CPC分类号	H01L51/5268 H01L27/322 H01L2251/5315 H01L51/5237 H01L51/5275 H01L51/5225 H01L51/5253		
代理人(译)	PARK, 常树		
优先权	2001307516 2001-10-03 JP		
其他公开文献	KR100495703B1		
外部链接	<a href="#">Espacenet</a>		

#### 摘要(译)

本发明涉及用于发光器件的微图案，其是通过简单工艺提高光耦合效率并防止漏光的发光器件，以及其制造方法和显示器件的目的使用相同的提供。确实如此。根据本发明的发光器件形成发光器件，其中具有不同光的光包括有机电致发光器件（有机电致发光显示器），衍射光栅或波带片，以及滤光器和出射光被控制就预定角度范围而言，由于从发光层发射的光穿过形成预定晶格距离的衍射光栅或区域板，或者它通过穿过滤光器反射并从发光层发射。并取出色调或颜色。关于有机电致发光器件（有机电致发光显示器），形成电极和发光层。有机电致发光显示器和图案。

